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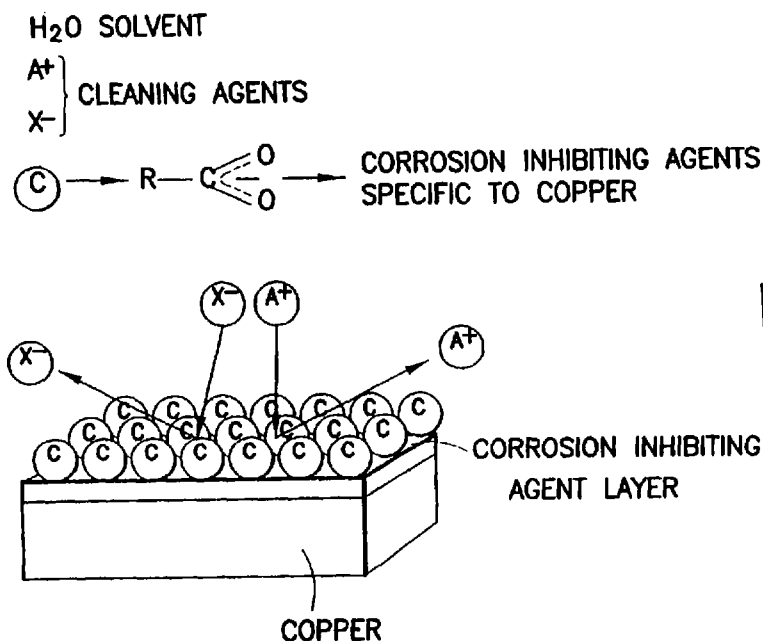
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(54) Title: SEMICONDUCTOR STRIPPING COMPOSITION CONTAINING 1,3-DICARBONYL COMPOUNDS



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(57) Abstract: A semiconductor wafer cleaning formulation, including 2-98 % wt. Organic amine, 0-50 % wt. Water, 0,1-60 % wt. 1,3-dicarbonyl compound chelating agent, 0-25 % wt. Of additional different chelating agent(s), 0.5-40 % wt. Nitrogen-containing carboxylic acid or an imine, and 2-98 % wt. Polar organic solvent. The formulations are useful to remove residue from wafers following a resist plasma ashing step, such as inorganic residue from semiconductor wafers containing delicate copper interconnecting structures.

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